ABSTRACT

A light-emitting device 100 has ITO transparent electrode layers 8, 10 used for applying drive voltage for light-emission to a light-emitting layer section 24, and is designed so as to extract light from the light-emitting layer section 24 through the ITO transparent electrode layers 8, 10. The light-emitting device 100 also has contact layers composed of In-containing GaAs, formed between the light-emitting layer section 24 and the ITO transparent electrode layers 8, 10, so as to contact with the ITO transparent electrode layers respectively. The contact layers 7, 9 are formed by annealing a stack 13 obtained by forming GaAs layers 7', 9' on the light-emitting layer section, and by forming the ITO transparent electrode layers 8, 10 so as to contact with the GaAs layers 7', 9', to thereby allow In to diffuse from the ITO transparent electrode layers 8, 10 into the GaAs layers 7', 9'. This provides a method of fabricating a light-emitting device, in which the ITO transparent electrode layers as the light-emission drive electrodes are bonded as being underlain by the contact layers, to thereby reduce contact resistance of these electrodes, and to thereby make the contact layers less susceptible to difference in the lattice constants with those of the light-emitting layer section during the formation thereof.